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March 1999



FDC6305N

Dual N-Channel 2.5V Specified PowerTrench[™] MOSFET

General Description

These N-Channel low threshold 2.5V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

Applications

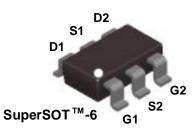
- Load switch
- DC/DC converter
- Motor driving

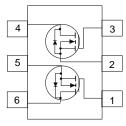
Features

• 2.7 A, 20 V.
$$R_{DS(ON)} = 0.08 \ \Omega @ V_{GS} = 4.5 \ V$$

 $\mathsf{R}_{_{\text{DS(ON)}}}$ = 0.12 Ω @ $\mathsf{V}_{_{\text{GS}}}$ = 2.5 V

- Low gate charge (3.5nC typical).
- Fast switching speed.
- High performance trench technology for extremely low $\rm R_{\rm DS(ON)}.$
- SuperSOTTM-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		<u>+</u> 8	V
ID	Drain Current - Continuous	(Note 1a)	2.7	А
	- Pulsed		8	
PD	Power Dissipation for Single Operation	(Note 1a)	0.96	W
		(Note 1b)	0.9	
		(Note 1c)	0.7	
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	۰C
Therma	I Characteristics			
R _{θJA}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	130	∘C/W
R _θ JC	Thermal Resistance, Junction-to-Case	(Note 1)	60	°C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
 .305	FDC6305N	7"	8mm	3000 units

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Parameter	Test Conditions	Min	Тур	Max	Units
racteristics					
Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	20			V
Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, Referenced to 25° C		14		mV/∘C
Zero Gate Voltage Drain Current	$V_{DS} = 16 V, V_{GS} = 0 V$			1	μA
Gate-Body Leakage Current, Forward	$V_{GS} = 8 V, V_{DS} = 0 V$			100	nA
Gate-Body Leakage Current, Reverse	V_{GS} = -8 V, V_{DS} = 0 V			-100	nA
acteristics (Note 2)					
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.4	0.9	1.5	V
Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-2.7		mV/∘C
Static Drain-Source On-Resistance	$V_{GS} = 4.5, I_D = 2.7 \text{ A}$ $V_{GS} = 4.5 I_D = 2.7 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = 2.5 \text{ V}, I_D = 2.2 \text{ A}$		0.060 0.095 0.085	0.080 0.128 0.120	Ω
On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	6			А
Forward Transconductance	$V_{DS} = 5 V, I_D = 2.7 A$		8		S
c Characteristics					
Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		310		pF
Output Capacitance	f = 1.0 MHz		80		pF
Reverse Transfer Capacitance			40		pF
ng Characteristics (Note 2)					
Turn-On Delay Time	$V_{DD} = 10 V, I_D = 1 A,$		5	15	ns
Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$	-	8.5	17	ns
Turn-Off Delay Time	1		11	20	ns
Turn-Off Fall Time	1		3	10	ns
Total Gate Charge	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 2.7 \text{ A},$		3.5	5	nC
-	V _{GS} = 4.5 V		0.55		nC
Gate-Source Charge					
Gate-Source Charge Gate-Drain Charge			0.95		nC
Gate-Drain Charge	d Maximum Ratings		0.95		nC
° °	-		0.95	0.8	nC A
	Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse acteristics (Note 2) Gate Threshold Voltage Gate Threshold Voltage Temperature Coefficient Static Drain-Source On-Resistance On-State Drain Current Forward Transconductance Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance Characteristics (Note 2) Turn-On Rise Time Turn-On Rise Time Turn-Off Delay Time	CoefficientVDS $= 16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$ Zero Gate Voltage Drain Current $V_{DS} = 16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$ Gate-Body Leakage Current, Forward $V_{GS} = 8 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{DS} = 10 \text{ L}, Referenced to 25^{\circ}C$ Gate Threshold Voltage Temperature Coefficient $V_{GS} = 4.5 \text{ I}_D = 2.7 \text{ A}$ Static Drain-Source On-Resistance $V_{GS} = 4.5 \text{ V}, D_D = 2.7 \text{ A}$ On-State Drain Current $V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$ Forward Transconductance $V_{DS} = 5 \text{ V}, I_D = 2.7 \text{ A}$ CharacteristicsInput CapacitanceInput Capacitance $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$ Reverse Transfer CapacitanceVDD = 10 \text{ V}, I_D = 1 \text{ A}, V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \OmegaTurn-On Rise Time $V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$ Turn-Off Delay TimeVDD = 10 \text{ V}, I_D = 1 \text{ A}, V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega	CoefficientVDSInterventVDSInterventZero Gate Voltage Drain CurrentVDS $V_{GS} = 0 V$ InterventGate-Body Leakage Current, ReverseVGS $V_{DS} = 0 V$ InterventGate-Body Leakage Current, ReverseVGS $V_{DS} = 0 V$ InterventGate Threshold VoltageVDS $V_{DS} = V_{GS}, I_D = 250 \mu A$ 0.4 Gate Threshold VoltageVDS $V_{DS} = V_{GS}, I_D = 250 \mu A$ 0.4 Gate Threshold VoltageVDS $V_{DS} = V_{GS}, I_D = 250 \mu A$ 0.4 Gate Threshold VoltageVDS $V_{DS} = 10 \mu A$, Referenced to $25^{\circ}C$ $V_{CS} = 4.5, I_D = 2.7 A$ Static Drain-SourceVGS $V_{GS} = 4.5, I_D = 2.7 A$ $V_{GS} = 2.5 V, I_D = 2.2 A$ On-ResistanceVGS $V_{DS} = 5 V, I_D = 2.7 A$ $V_{CS} = 2.5 V, I_D = 2.2 A$ On-State Drain CurrentVGS $V_{DS} = 5 V, I_D = 2.7 A$ $V_{DS} = 5 V, I_D = 2.7 A$ CharacteristicsInput Capacitance $V_{DS} = 5 V, I_D = 2.7 A$ $V_{DS} = 5 V, I_D = 2.7 A$ Input CapacitanceVDS $V_{DS} = 10 V, V_{CS} = 0 V, I_D = 1.0 M Hz$ $V_{DS} = 10 V, V_{CS} = 0 V, I_D = 1.0 M Hz$ Characteristics(Note 2) $V_{DD} = 10 V, I_D = 1 A, V_{CS} = 0 Q$ $V_{CS} = 4.5 V, R_{GEN} = 6 \Omega$ Turn-On Delay TimeVDS = 10 V, V_GS = 6 \Omega $V_{CS} = 4.5 V, R_{GEN} = 6 \Omega$ $V_{CS} = 4.5 V, R_{GEN} = 6 \Omega$	CoefficientVDS16 V, VGS0Zero Gate Voltage Drain Current $V_{DS} = 16$ V, $V_{GS} = 0$ V0Gate-Body Leakage Current, Forward $V_{GS} = 8$ V, $V_{DS} = 0$ V0Gate-Body Leakage Current, Reverse $V_{GS} = -8$ V, $V_{DS} = 0$ V0cateristics (Note 2)Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \ \mu$ A0.40.9Gate Threshold Voltage $I_D = 250 \ \mu$ A, Referenced to 25°C-2.7Temperature Coefficient $V_{GS} = 4.5$, $I_D = 2.7$ A, $T_J = 125°C$ 0.060On-Resistance $V_{GS} = 4.5$, $I_D = 2.7$ A, $T_J = 125°C$ 0.085On-State Drain Current $V_{GS} = 4.5$ V, $V_{DS} = 5$ V6Forward Transconductance $V_{DS} = 5$ V, $I_D = 2.7$ A8CharacteristicsInput Capacitance $V_{DS} = 10$ V, $V_{GS} = 0$ V,310Output Capacitance $V_{DS} = 10$ V, $V_{GS} = 0$ V,40GCharacteristics (Note 2)Turn-On Delay Time $V_{DD} = 10$ V, $I_D = 1$ A,5Turn-On Rise Time $V_{GS} = 4.5$ V, $R_{GEN} = 6$ Ω 8.5	$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$

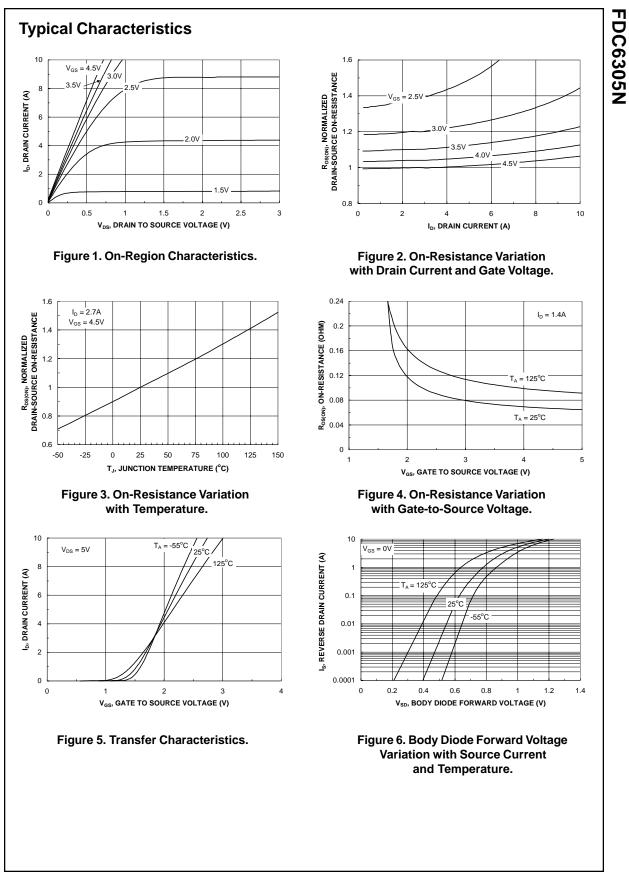




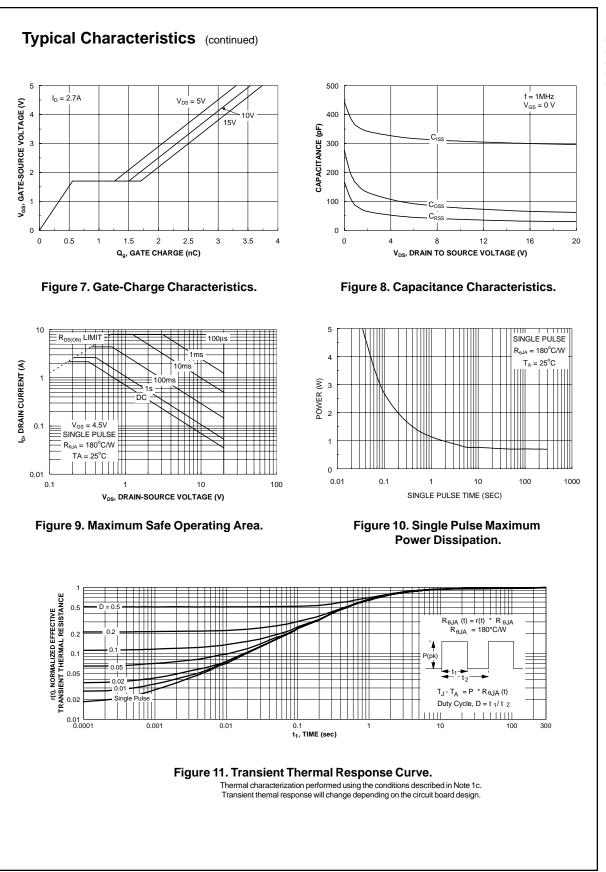
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

FDC6305N



FDC6305N, Rev. C



FDC6305N

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